

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

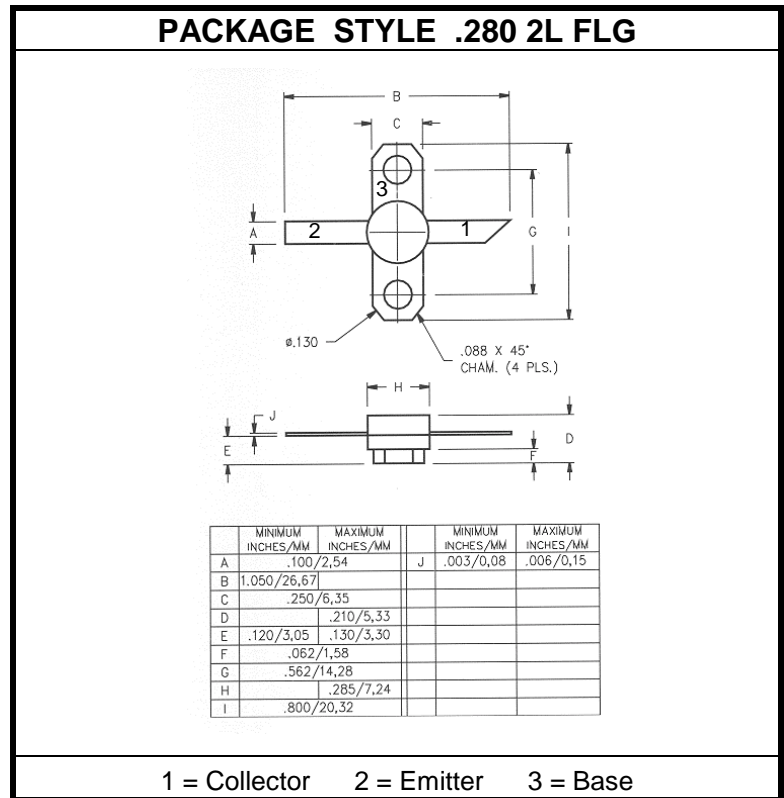
The **ASI MSC1035M** is Designed for Class C, DME/TACAN Applications up to 1150 MHz.

**FEATURES:**

- Class C Operation
- $P_G = 10.7$  dB at 35 W/1150 MHz
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

$I_C$	3.0 A PEAK
$V_{CB}$	65 V
$P_{DISS}$	150 W PEAK
$T_J$	-65 °C to +250 °C
$T_{STG}$	-65 °C to +200 °C
$\theta_{JC}$	1.0 °C/W


**CHARACTERISTICS**  $T_C = 25$  °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CBO}$	$I_C = 10$ mA	65			V
$BV_{CER}$	$I_C = 10$ mA $R_{BE} = 10$ $\Omega$	65			V
$BV_{EBO}$	$I_E = 1.0$ mA	3.5			V
$I_{CES}$	$V_{CB} = 50$ V			5.0	mA
$h_{FE}$	$V_{CE} = 5.0$ V $I_C = 500$ mA	15		120	---
$P_G$	$V_{CC} = 50$ V $P_{OUT} = 35$ W $f = 1025 - 1150$ MHz	10.7	11.2		dB
$\eta_c$	$P_{IN} = 3.0$ W	43	48		%

Pulse width = 10  $\mu$ Sec, Duty Cycle = 1 %